



Future Normal in Semiconductor

2025년 2월 13일(목), 09:00-10:45

Room K(하트 I), 6층

G. Device & Process Modeling, Simulation and Reliability 분과

011_[TK1-G] Device Characterization & Modeling 1

좌장: 이재우 교수(고려대학교), 김세영 교수(포항공과대학교)

<p>초청 TK1-G-1 09:00-09:30</p>	<p>Multiscale Investigation for Semiconductor Process Design with Computational Science and Artificial Intelligence Byungjo Kim UNIST</p>
<p>TK1-G-2 09:30-09:45</p>	<p>Ballistic Transport in State-of-the Art $\text{In}_{0.65}\text{Ga}_{0.35}\text{As}/\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ Quantum-Well HEMTs at Room and Cryogenic Temperatures Seung-Woo Son, In-Geun Lee, Min-Seo Yu, Su-Min Choi, Yong-Soo Jeon, Sang-Pyeong Son, Ji-Hoon Yoo, Sang-Ki Yun, Jae-Hak Lee, and Dae-Hyun Kim School of Electronic and Electrical Engineering Kyungpook National University</p>
<p>TK1-G-3 09:45-10:00</p>	<p>Design Optimization of Capacitor-Based Synaptic Cells for Efficient Analog Neural Network Training Byoungwoo Lee, Wonjae Ji, Hyejin Kim, Seungmin Han, Junyoung Choi, and Seyoung Kim Department of Material Science and Engineering, POSTECH</p>
<p>TK1-G-4 10:00-10:15</p>	<p>Exploring the Channel Thickness Effect on Carrier Transport Mechanism of Schottky Contacts in Ultrathin α-IGZO TFTs Hongseung Lee¹, Jaewook Yoo¹, YuJun Roh¹, Hyeonjun Song¹, Soyeon Kim¹, Seongbin Lim¹, Seohyeon Park¹, Minah Park¹, Sojin Jung¹, Jin-Ha Hwang², Kiyoung Lee², and Hagyoul Bae¹ ¹Jeonbuk National University, ²Hongik University</p>
<p>TK1-G-5 10:15-10:30</p>	<p>Exploring the Deuterium Annealing Effect on Persistent Photoconductivity Related to Subgap DOS in IGZO TFTs Hyeonjun Song¹, Jaewook Yoo¹, Soyeon Kim¹, Hongseung Lee¹, Seongbin Lim¹, Minah Park¹, Seohyeon Park¹, Sojin Jung¹, Jun-Young Park², Yoon Kyeong Lee¹, Kiyoung Lee³, and Hagyoul Bae¹ ¹Jeonbuk National University, ²Chungbuk National University, ³Hongik University</p>



제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

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TK1-G-6
10:30-10:45

Analysis on Effect of Proton Irradiation on Schottky-Barrier a-IGZO TFTs using TCAD Simulation

Eunchong Kim¹, Hyunwook Jeong¹, Yubin Choi¹, Junseong Park¹, Haesung Kim¹, Hyojin Yang¹, Sung-Jin Choi¹, Dae Hwan Kim¹, Dong Myong Kim², Sung Yun Woo³, and Jong-Ho Bae¹

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